DATA SHEET
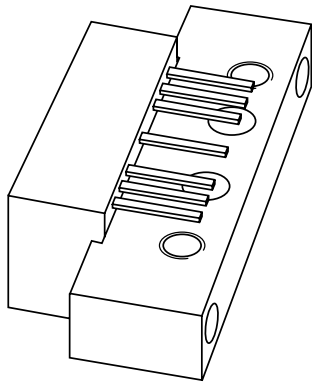
BGD712
750 MHz, 18.5 dB gain power doubler amplifier

Product specification

Supersedes data of 2001 Oct 29

2001 Nov 02

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FEATURES

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
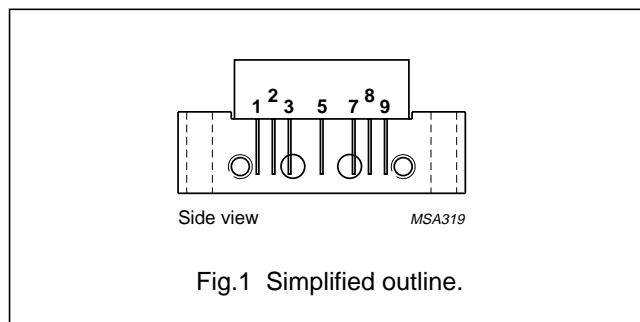- Gold metallization ensures excellent reliability.

APPLICATIONS

- CATV systems operating in the 40 to 750 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating with a voltage supply of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2, 3	common
5	$+V_B$
7, 8	common
9	output

Side view   *MSA319*

Fig.1 Simplified outline.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	f = 45 MHz	18.2	18.8	dB
		f = 750 MHz	19	20	dB
I_{tot}	total current consumption (DC)	V_B = 24 V	380	410	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_B	supply voltage	–	30	V
V_i	RF input voltage	–	70	dBmV
T_{stg}	storage temperature	–40	+100	°C
T_{mb}	operating mounting base temperature	–20	+100	°C

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CHARACTERISTICS

Bandwidth 40 to 750 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 45 MHz	18.2	18.5	18.8	dB
		f = 750 MHz	19	19.5	20	dB
SL	slope straight line	f = 45 to 750 MHz; note 1	0.5	1	1.5	dB
FL	flatness straight line	f = 45 to 100 MHz	–	–	±0.35	dB
		f = 100 to 700 MHz	–	–	±0.5	dB
		f = 700 to 750 MHz	–	–	±0.15	dB
S_{11}	input return losses	f = 45 to 80 MHz	23	–	–	dB
		f = 80 to 160 MHz	23	–	–	dB
		f = 160 to 320 MHz	21	–	–	dB
		f = 320 to 550 MHz	20	–	–	dB
		f = 550 to 650 MHz	20	–	–	dB
		f = 650 to 750 MHz	19	–	–	dB
		f = 750 to 790 MHz	17	–	–	dB
S_{22}	output return losses	f = 45 to 80 MHz	23	–	–	dB
		f = 80 to 160 MHz	23	–	–	dB
		f = 160 to 320 MHz	20	–	–	dB
		f = 320 to 550 MHz	20	–	–	dB
		f = 550 to 650 MHz	19	–	–	dB
		f = 650 to 750 MHz	19	–	–	dB
		f = 750 to 790 MHz	17	–	–	dB
S_{21}	phase response	f = 50 MHz	−45	–	+45	deg
CTB	composite triple beat	112 channels flat; $V_o = 44$ dBmV; $f_m = 745.25$ MHz	–	–	−62	dB
		79 channels flat; $V_o = 44$ dBmV; $f_m = 547.25$ MHz	–	–	−68	dB
		79 channels; $f_m = 445.25$ MHz; $V_o = 49.3$ dBmV at 547 MHz; note 2	–	–	−63	dB
X_{mod}	cross modulation	112 channels flat; $V_o = 44$ dBmV; $f_m = 55.25$ MHz	–	–	−63	dB
		79 channels flat; $V_o = 44$ dBmV; $f_m = 55.25$ MHz	–	–	−69	dB
		79 channels; $f_m = 745.25$ MHz; $V_o = 49.3$ dBmV at 547 MHz; note 2	–	–	−60	dB

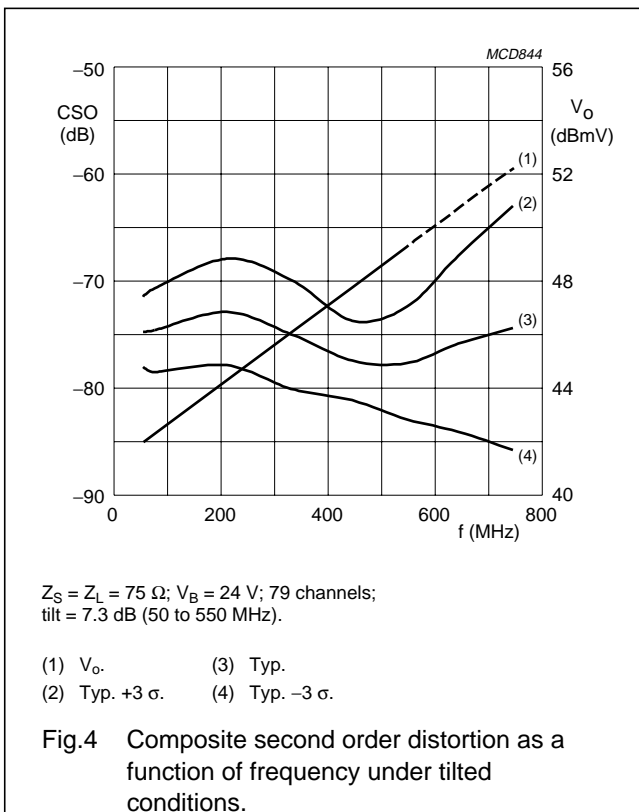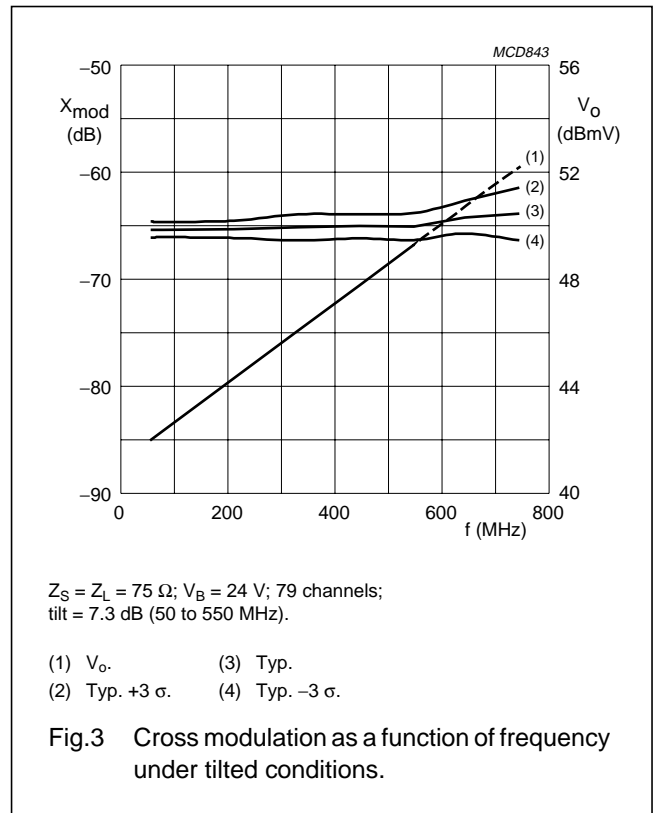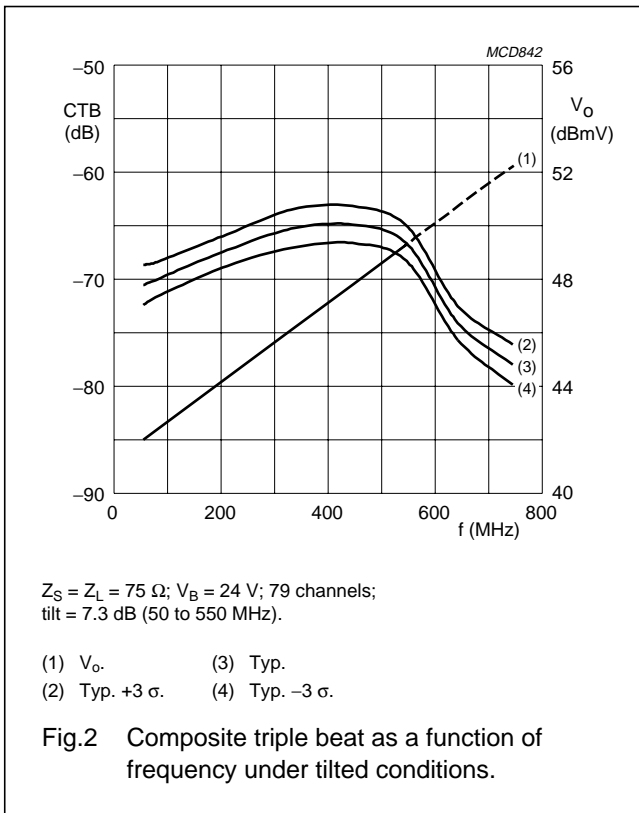## 750 MHz, 18.5 dB gain power doubler amplifier

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
CSO	composite second order distortion	112 channels flat; V_o = 44 dBmV; f_m = 746.5 MHz	–	–	–63	dB
		79 channels flat; V_o = 44 dBmV; f_m = 548.5 MHz	–	–	–68	dB
		79 channels; f_m = 746.5 MHz; V_o = 49.3 dBmV at 547 MHz; note 2	–	–	–62	dB
d_2	second order distortion	note 3	–	–	–74	dB
V_o	output voltage	d_{im} = –60 dB; note 4	64	–	–	dBmV
NF	noise figure	f = 50 MHz	–	–	5.5	dB
		f = 550 MHz	–	–	5.5	dB
		f = 750 MHz	–	–	7	dB
I_{tot}	total current consumption (DC)	note 5	380	395	410	mA

Notes

1. Slope straight line is defined as gain at 750 MHz − gain at 45 MHz.

2. Tilt = 7.3 dB (55 to 547 MHz).

3. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 691.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 746.5 MHz.

4. Measured according to DIN45004B:
   f_p = 740.25 MHz; $V_p = V_o$;
   f_q = 747.25 MHz; $V_q = V_o$ −6 dB;
   f_r = 749.25 MHz; $V_r = V_o$ −6 dB;
   measured at $f_p + f_q − f_r$ = 738.25 MHz.

5. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

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$Z_S = Z_L = 75\ \Omega$; $V_B = 24$ V; 79 channels;
tilt = 7.3 dB (50 to 550 MHz).

(1) V_o.   (3) Typ.
(2) Typ. +3 σ.   (4) Typ. −3 σ.

Fig.2   Composite triple beat as a function of
        frequency under tilted conditions.

$Z_S = Z_L = 75\ \Omega$; $V_B = 24$ V; 79 channels;
tilt = 7.3 dB (50 to 550 MHz).

(1) V_o.   (3) Typ.
(2) Typ. +3 σ.   (4) Typ. −3 σ.

Fig.3   Cross modulation as a function of frequency
        under tilted conditions.

$Z_S = Z_L = 75\ \Omega$; $V_B = 24$ V; 79 channels;
tilt = 7.3 dB (50 to 550 MHz).

(1) V_o.   (3) Typ.
(2) Typ. +3 σ.   (4) Typ. −3 σ.

Fig.4   Composite second order distortion as a
        function of frequency under tilted
        conditions.

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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes;
2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads   **SOT115J**
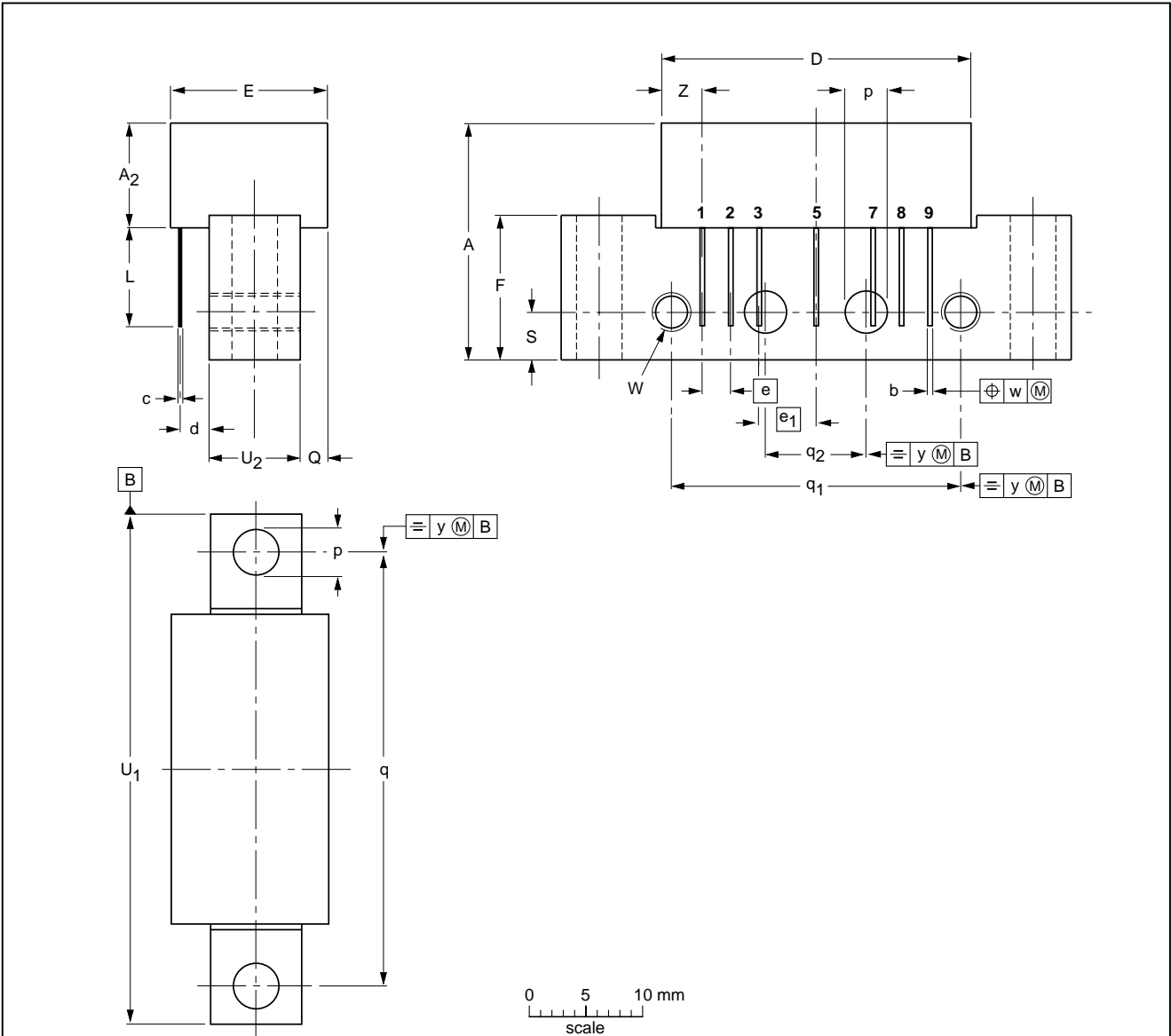
DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A2 max.	b	c	D max.	d max.	E max.	e	e1	F	L min.	p	Q max.	q	q1	q2	S	U1 max.	U2	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115J						99-02-06

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DATA SHEET STATUS

DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.

2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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